

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A semiconductor device, ~~comprising~~ consisting of a plastic substrate, a layer that can be damaged by pulsed radiation, a narrowband reflective coating layer, a transparent layer, and a layer fabricated with pulsed radiation, with said semiconductor device consisting of the structural elements located in the following order:

a plastic substrate,

a layer that can be damaged by said pulsed radiation, said layer that can be damaged by said pulsed radiation positioned above said plastic substrate and operatively connected to said layer fabricated with pulsed radiation,

a narrowband reflective coating layer, said narrowband reflective coating layer positioned above said layer that can be damaged by pulsed radiation, positioned above said plastic substrate, and operatively connected to said layer that can be damaged by said pulsed radiation,

a transparent layer, said transparent layer located directly above said narrowband reflective coating layer, and

a layer fabricated with pulsed radiation, said layer fabricated with pulsed radiation positioned above said plastic substrate,

wherein said narrowband reflective coating layer is positioned over said layer that can be damaged by said pulsed radiation for reflecting said pulsed radiation and protecting said layer that can be damaged by said pulsed radiation.

2. (Original) The semiconductor device of claim 1 wherein said layer that can be damaged by said pulsed radiation is low temperature plastic.

3. (Currently Amended) The semiconductor device of claim 1 wherein said narrowband reflective coating layer is single layer ~~or multiple layers for narrowband reflection~~.

4. (Currently Amended) The semiconductor device of claim 3 1 wherein said narrowband reflective coating layer is a single layer of narrow band reflectance coating.

5. (Cancelled)

6. (Cancelled)

7. (Cancelled)

8. (Cancelled)

9. (Cancelled)

10. (Currently Amended) The semiconductor device of claim 1 wherein said layer that can be damaged by said pulsed radiation is low temperature plastic, said narrowband reflective coating layer is single layer ~~or multiple layers~~ for of narrowband reflection reflective coating, and said layer fabricated with pulsed radiation is a layer that has been fabricated with high intensity radiation sources.

11. (Previously Presented) The semiconductor device of claim 1 wherein said layer that can be damaged by said pulsed radiation is polyester.

12. (Cancelled)

13. (Cancelled)